					Docket Number (Optional) OIP.024D2	A	Application Number . NEW				
•	INFO	DEMATION DISCLOSURE (Use several sheets if necessa	1	Applicant(s) Akira Takahashi		10,		52			
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and tot considered. Include copy of this form with next communication to applicant.											

				Docket Number (Optional) OIP.024D	Application Number NEW				
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				U.S. PAT	ENT DOCUMENTS				
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